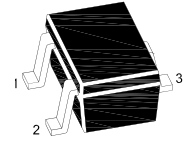
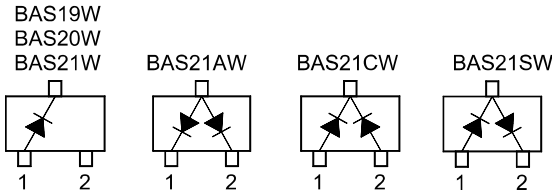


Silicon Epitaxial Planar Diodes

High Voltage Switching Diodes



SOT-323 Plastic Package



Marking Code	
BAS19W	KT1
BAS20W	KT2
BAS21W	KT3
BAS21AW	F2
BAS21CW	F3
BAS21SW	F4

Absolute Maximum Ratings (Ta= 25°C)

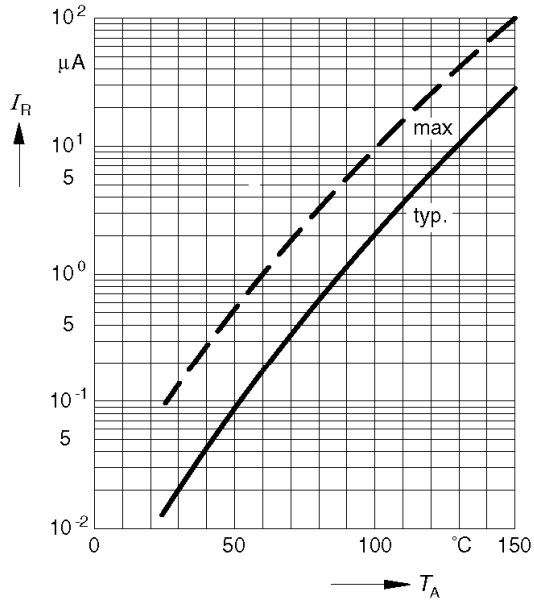
Parameter	Symbol	Value	Unit
Reverse Voltage	BAS19W BAS20W BAS21W	120 200 250	V
Continuous Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 μs	0.5 2.5	A
Total Device Dissipation	P_{tot}	250	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	°C

Characteristics at Ta= 25°C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu A$ at $I_R = 100 \mu A$ at $I_R = 100 \mu A$	BAS19W BAS20W BAS21W	120 200 250	- - -	V
Forward Voltage at $I_F = 100 mA$ at $I_F = 200 mA$	V_F	- -	1 1.25	V
Reverse Current at $V_R = 100 V$ at $V_R = 150 V$ at $V_R = 200 V$ at $V_R = 100 V, T_j = 150^\circ C$ at $V_R = 150 V, T_j = 150^\circ C$ at $V_R = 200 V, T_j = 150^\circ C$	BAS19W BAS20W BAS21W BAS19W BAS20W BAS21W	- - - - - -	0.1 0.1 0.1 100 100 100	μA
Total Capacitance at $V_R = 0, f = 1 MHz$	C_{tot}	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30 mA, I_{R(REC)} = 3 mA, R_L = 100 \Omega$	t_{rr}	-	50	ns

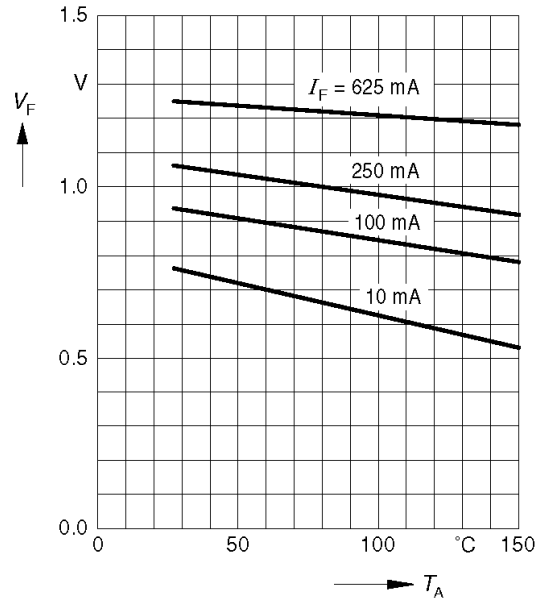
Reverse current $I_R = f(T_A)$

$V_R = 200V$

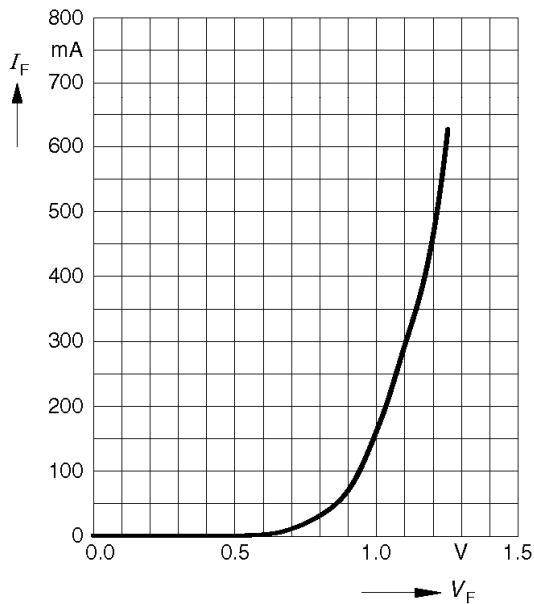


Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$

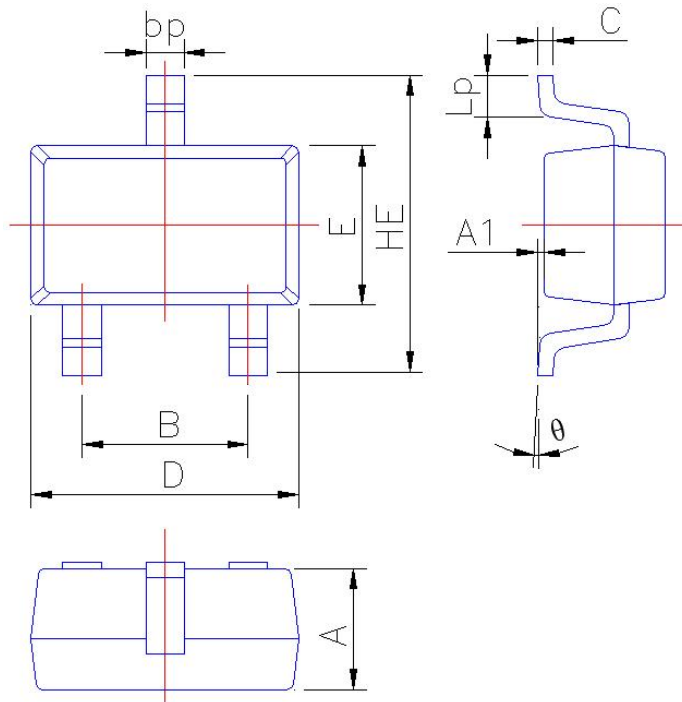


Forward current $I_F = f(V_F)$



Package Outline

SOT-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-323	Tape/Reel, 7" reel	3000	EIA-481-1

单击下面可查看定价，库存，交付和生命周期等信息

[>>YFW\(佑风微\)](#)